

IN THE CLAIMS

1 (Currently Amended). A method comprising:
developing a patterned photoresist;
absorbing ~~applying~~ a plasticizer in a supercritical fluid into ~~to~~ the surface of said
patterned photoresist after developing the photoresist; and
reflowing the photoresist after absorbing ~~applying~~ the plasticizer.

Claim 2 (Canceled).

3 (Previously Presented). The method of claim 1 including applying the plasticizer in
a supercritical carbon dioxide fluid.

Claims 4 and 5 (Canceled).

6 (Original). The method of claim 1 including applying the plasticizer with the develop
rinse.

7 (Original). The method of claim 1 including applying a plasticizer that improves the
etch resistance of the photoresist.

8 (Original). The method of claim 1 wherein applying a plasticizer includes diffusing a
plasticizer into the photoresist.

9 (Original). The method of claim 8 including diffusing a plasticizer in a vapor phase
into the photoresist.

10 (Original). The method of claim 1 including controlling the amount of reflow by
volatilizing the plasticizer during reflow.

11 (Original). The method of claim 1 including applying the plasticizer in liquid carbon dioxide.

12 (Original). The method of claim 1 including controlling the amount of reflow by cooling the photoresist.

Claims 13-27 (Canceled).